

< C band internally matched power GaAs FET >

MGFC39V5964A

5.9 - 6.4 GHz BAND / 8W

DESCRIPTION

The MGFC39V5964A is an internally impedance-matched GaAs power FET especially designed for use in 5.9 - 6.4 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) system

- High output power P1dB=8W (TYP.) @f=5.9 - 6.4GHz
- High power gain GLP=10.5dB (TYP.) @f=5.9 - 6.4GHz
- High power added efficiency P.A.E.=30% (TYP.) @f=5.9 - 6.4GHz
- Low distortion [item -51] IM3=-45dBc (TYP.) @Po=28dBm S.C.L

APPLICATION

• item 01: 5.9 - 6.4 GHz band power amplifier

• item 51: 5.9 - 6.4 GHz band digital radio communication

QUALITY

• IG

RECOMMENDED BIAS CONDITIONS

• VDS=10V • ID=2.4A Refer to Bias Procedure RG=50ohm

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit				
VGDO	Gate to drain breakdown voltage	-15	V				
VGSO	Gate to source breakdown voltage	-15	V				
ID	Drain current	7.5	Α				
IGR	Reverse gate current	-20	mA				
IGF	Forward gate current	42	mA				
PT *1	Total power dissipation	42.8	W				
Tch	Cannel temperature	175	°C				
Tstg	Storage temperature	-65 to +175	ç				
*1 · Tc=25°C							

OUTLINE DRAWING Unit: millimeters 21.0 +/-0.3 12.9 +/-0.2 (3)

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Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits		Unit	
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	-	7.5	Α
gm	Transconductance	VDS=3V,ID=2.2A	-	2	i	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=20mA	-	-	-4.5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=2.4A	38	39.5	i	dBm
GLP	Linear Power Gain	f=5.9 - 6.4GHz	8	10.5	-	dB
ID	Drain current		-	-	3	Α
P.A.E.	Power added efficiency		-	30	-	%
IM3 *2	3rd order IM distortion		-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	-	3.5	°C/W

^{*2 :}item -51 ,2 tone test,Po=28dBm Single Carrier Level ,f=6.4GHz,delta f=10MHz

^{*3:} Channel-case

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